

IN THE TITLE:

Please replace the current title with the following replacement title:

--METHOD OF FORMING AN OXIDE LAYER--

IN THE SPECIFICATION:

Please amend paragraph [0047] as follows:

[0047] Referring again to FIG. 4, in action 404 coating material 504 can be layered on wafer 506 to any desired thickness, for example, a thickness of between about 1000 Å and about 1 μm ~~5000 Å~~.

Please amend paragraph [0050] as follows:

[0050] In some embodiments, in order to grow the oxide layer to a desired thickness, the process can return at action 408 to action 404 such that additional layers of between 1000 Å and 1 μm ~~5000 Å~~ of coating material 504 can be added to the previously baked layer. Actions 404 and 406 of process 400 can repeat until a desired thickness of a baked material is formed. For example, actions 404 and 406 can be repeated until the baked layer is between about 0.5 μm and 20 μm. In these embodiments, after each additional layer of coating material 504 is added, the wafer can again be subjected to the first heat treatment (Action 406).